



JMD120KD16T1W

Features

- A package of series of two diodes
- Heat transfer through alumina ceramic and metal substrate
- Welding by vacuum welding technology,

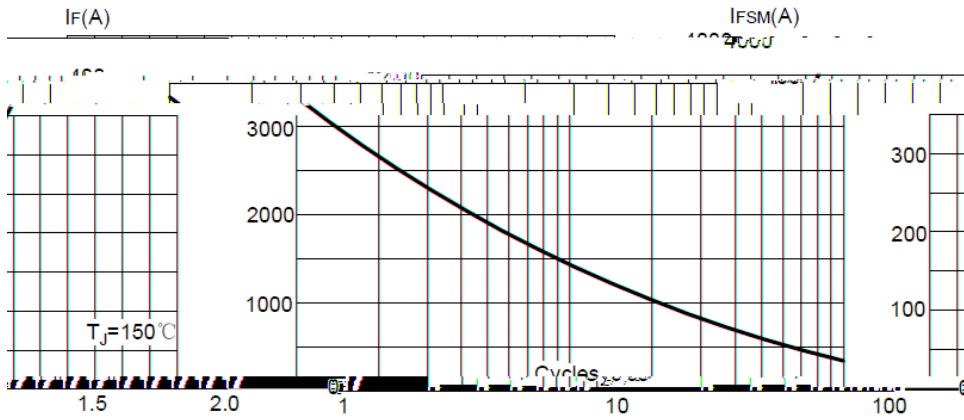
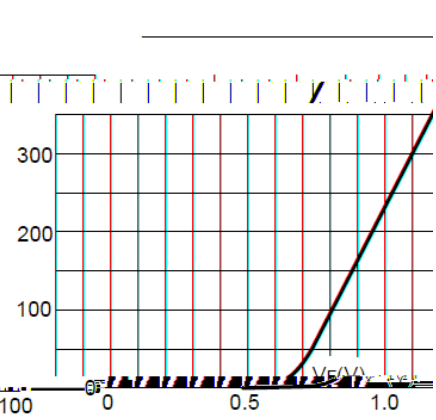
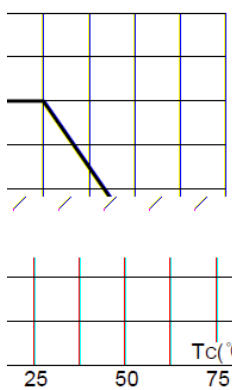
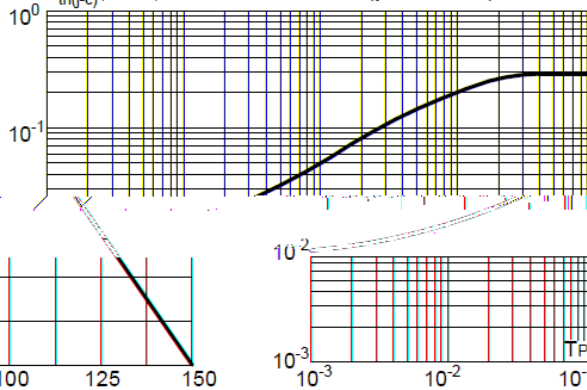
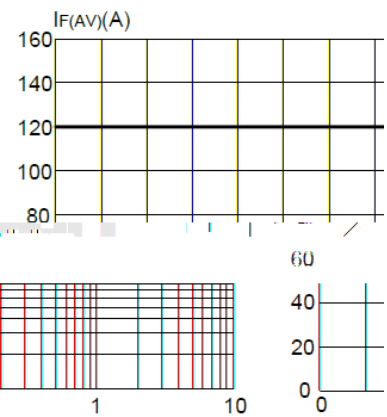
Product Summary



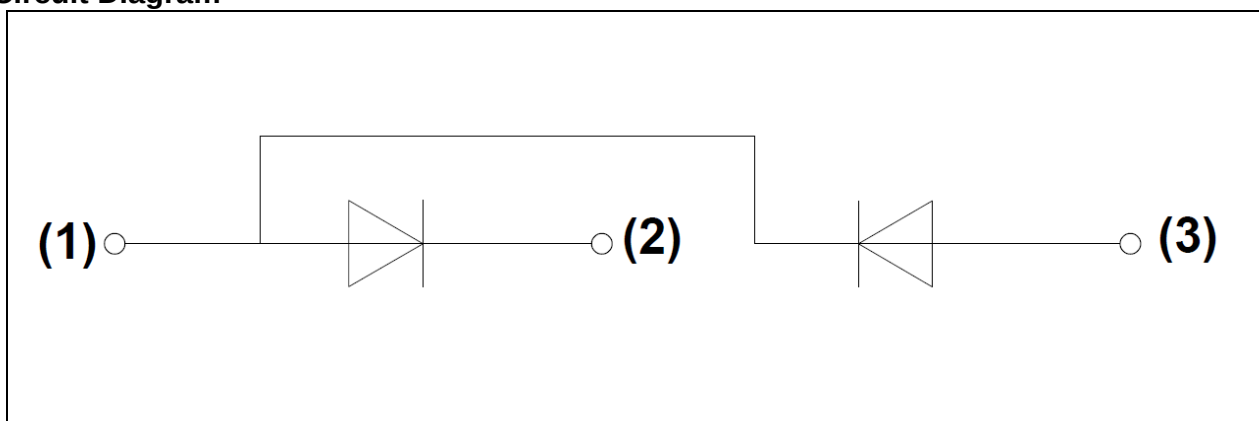
Electrical Characteristics (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Peak forward voltage	$I_F = 360\text{mA}$, $T_J \leq 25^\circ\text{C}$	$V_{F_{PK}}$	1.9	2.0	2.1	V
Reverse leakage current	$V_R = V_{RRM}$, $T_J \leq 25^\circ\text{C}$	$I_{R_{LEAK}}$	0	0	0	μA

Typical Electrical & Thermal Characteristics

FIG.1: Forward characteristics(per diode)

FIG.2: Peak on-state surge current

FIG.3: Forward current vs. case temperature

FIG.4: Maximum transient thermal impedance
 $R_{th(j-c)}$ (°C/W) Junction-to-case(per diode)

FIG.3: Forward current vs. case temperature


Circuit Diagram







Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Semiconductor Co., Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. This information in this document is subject to change without prior notice. Notwithstanding this, Jiangsu JieJie will fully comply with the terms outlined in a signed agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document is the initial release, dated 16 April 2026. This document supersedes and replaces all information previously supplied.

 is registered trademark of Jiangsu JieJie Semiconductor Co., Lt ©2026 Jiangsu JieJie Semiconductor Co., Ltd. All rights reserved.